

#### ABSTRACT OF THE DISCLOSURE

A semiconductor device and a method of manufacturing the device includes a first buried wiring, a second buried wiring formed as a layer different from the first buried wiring, a contact hole, which is formed between the first buried wiring and the second buried wiring and is filled with a wiring material for electrically connecting the first buried wiring and the second buried wiring therethrough, and a dummy hole, which has a hole diameter different from the contact hole, is so formed in vicinity of the contact hole as to connect the first buried wiring, and is filled with a wiring material therein.